

## ECPLC0511T1

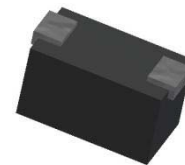
### Low-Capacitance Bidirectional Micro Packaged TVS Diodes for ESD Protection

The ECPLC0511T1 is designed with ECORE Punch-Through process TVS technology to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space comes at a premium. Also because of its low capacitance, it is suited for use in high frequency designs such as USB 2.0 high speed, VGA, DVI, SDI and other high speed line applications.

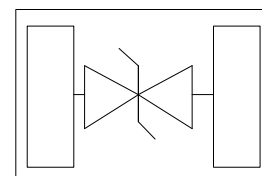
This series has been specifically designed to protect sensitive components which are connected to data and transmission lines from overvoltage caused by ESD(electrostatic discharge), and EFT (electrical fast transients).

#### Features

- Peak Power Dissipation – 50 W (8 x 20 us Waveform)
- Stand-off Voltage: 5.0 V
- Low capacitance for high-speed interfaces
- No insertion loss to 1.0GHz
- Replacement for MLV (0402)
- Protects I/O Port
- Low Clamping Voltage
- Low Leakage
- Low Capacitance
- Response Time is < 1 ns
- Meets MSL 1 Requirements
- ROHS compliant



**DFN1006**



#### Main applications

- High Speed Line :USB1.0/2.0, VGA, DVI, SDI,
- Serial and Parallel Ports
- Notebooks, Desktops, Servers
- Projection TV
- Cellular handsets and accessories
- Portable instrumentation
- Peripherals

#### Protection solution to meet

- IEC61000-4-2 (ESD) ±15kV (air), ±8kV (contact)
- IEC61000-4-4 (EFT) 40A (5/50ns)

#### Ordering Information

Device	Qty per Reel	Reel Size
ECPLC0511T1	5000/10000pcs	7inch

### Maximum ratings (Tamb=25°C Unless Otherwise Specified)

Parameter	Symbol	Value	Unit
Peak Pulse Power (tp=8/20µs waveform)	P <sub>PPP</sub>	50	Watts
Peak pulse current (tp=8/20µs waveform)	I <sub>PP</sub>	3	A
ESD Rating per IEC61000-4-2:	Contact	8	KV
	Air	15	
Lead Soldering Temperature	T <sub>L</sub>	260 (10 sec.)	°C
Operating Temperature Range	T <sub>J</sub>	-55 ~ 150	°C
Storage Temperature Range	T <sub>STG</sub>	-55 ~ 150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

\*Other voltages may be available upon request.

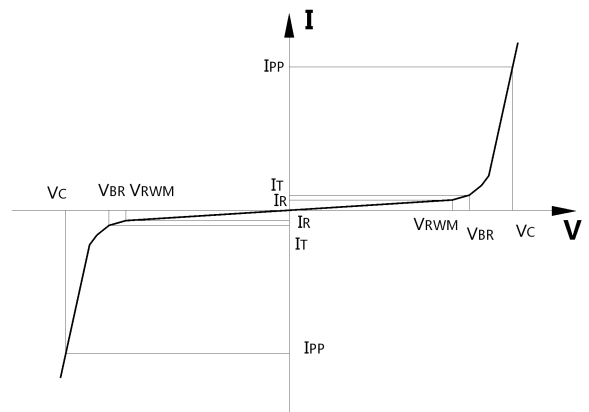
1. Non-repetitive current pulse, per Figure 1.

### Electrical characteristics (Tamb=25°C Unless Otherwise Specified)

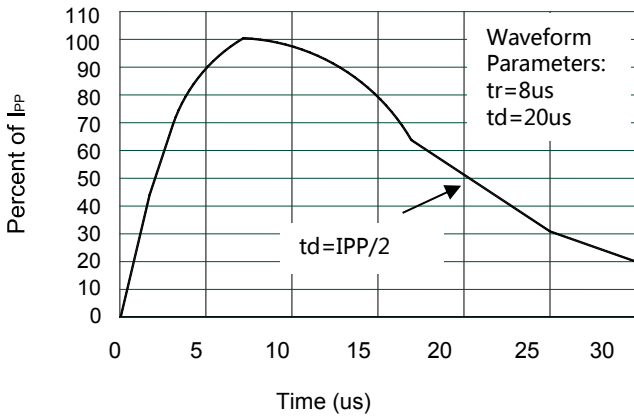
Device	V <sub>RWM</sub> (V)	I <sub>R</sub> @ V <sub>RWM</sub> (uA)	V <sub>BR</sub> @1 mA (V)		V <sub>C</sub> @3 A (V)		Capacitance @ V <sub>R</sub> = 0 V, 1 MHz (pF)	
		Max	Min	Max	Typ	Max	Typ	Max
		ECPLC0511T1	5.0	1	5.6	7.8	10.6	15

Junction capacitance is measured in V<sub>R</sub>=0V, F=1MHz

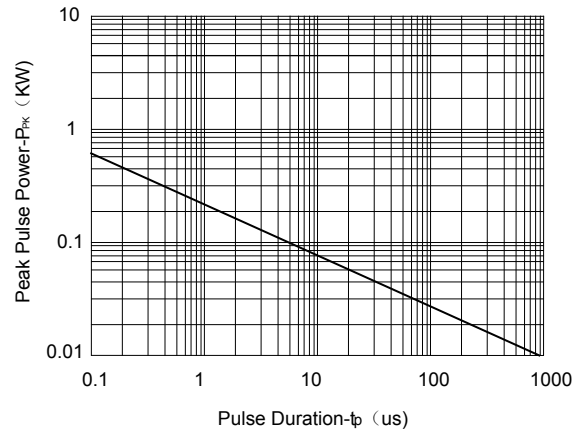
Symbol	Parameter
V <sub>RWM</sub>	Working Peak Reverse Voltage
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
V <sub>C</sub>	Clamping Voltage @ I <sub>PP</sub>
I <sub>T</sub>	Test Current
I <sub>RM</sub>	Leakage current at V <sub>RWM</sub>
I <sub>PP</sub>	Peak pulse current
C <sub>O</sub>	Off-state Capacitance
C <sub>J</sub>	Junction Capacitance



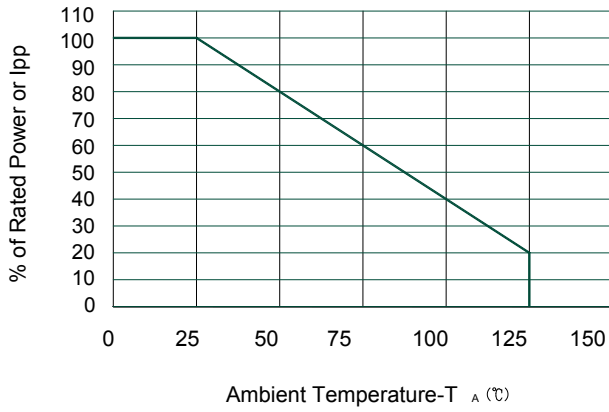
**Typical electrical characterist applications**



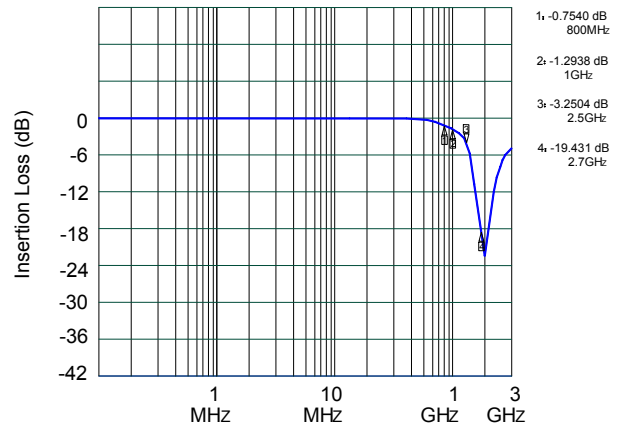
**Pulse Waveform**



**Non-Repetitive Peak Pulse Power vs. Pulse Time**



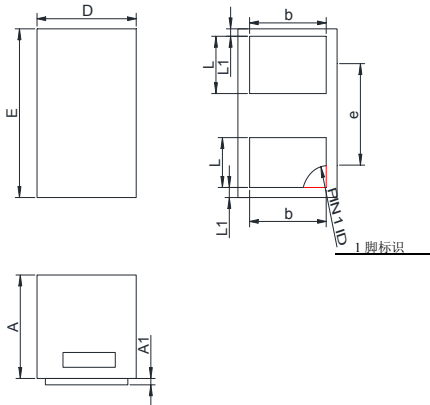
**Power Derating Curve**



**Insertion Loss S21**

Package Information

DFN1006



DIM	Millimeters	
	Min	Max
A	0.40	0.50
A1	0.00	0.05
D	0.55	0.65
E	0.95	1.05
b	0.40	0.60
e	0.65TYP	
L	0.15	0.35
L1	0.05REF	

Recommended Pad outline

